

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	49	memory with (inversion near (layer\$1 film\$1)) with ((diffus\$3 dop\$3 implant\$3) near (region\$1 area\$1 layer\$1 film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/08/08 10:01
L2	14	("4185318" "4527259" "4554643" "4868632" "5357134" "5408115" "5467308" "5763308" "5768192" "5859459" "5877523" "5923978" "6348387" "6563151").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/08 09:48
L3	7	("4527259" "5357134" "5408115" "5467308" "5763308" "5859459" "5923978").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/08 09:51
L4	218	memory same (inversion near (layer\$1 film\$1)) same ((diffus\$3 dop\$3 implant\$3) near (region\$1 area\$1 layer\$1 film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/08/08 10:09
L5	53	4 and (charge near storage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/08/08 10:10
L6	1363	memory and (inversion near (layer\$1 film\$1)) and ((diffus\$3 dop\$3 implant\$3) near (region\$1 area\$1 layer\$1 film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/08/08 10:38
L7	321	6 and (charge near storage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/08/08 10:10
L8	281	7 and electrode\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/08/08 10:11
L9	0	memory and (inversion near (layer\$1 film\$1)) and ((diffus\$3 dop\$3 implant\$3) near (region\$1 area\$1 layer\$1 film\$1)) and (charge adj storage\$1) and electrode\$1 and (voltage potential) and conductance and information and characteristic.CLM.	US-PGPUB; USPAT	OR	ON	2005/08/08 10:42

L10	3	memory and (inversion near (layer\$1 film\$1)) and ((diffus\$3 dop\$3 implant\$3) near (region\$1 area\$1 layer\$1 film\$1)) and (charge adj storage\$1) and electrode\$1 and (voltage potential) and conductance.CLM.	US-PGPUB; USPAT	OR	ON	2005/08/08 10:42
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